

SPECIFICATION OF LED CHIP C660-30M [RED]

1) Commodity Type and Physical Characteristics.

1. Material	GaAlAs/GaAlAs(DDH)		
2. Electrode	Top Side	N (cathode)side	:Au Alloy/Al Pad
	Bottom Side	P (anode)side	:Au Alloy
3. Electrode Pattern	Fig.1		
4. Chip Size	Fig.2		
5. Chip Thickness	Fig.2		
6. Emission Area	Fig.2		

2) Electro-Optical Characteristics [Ta=25°C]

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.9	2.3	V
Reverse Current	Ir	Vr=5V			10	uA
Brightness	Iv	If=20mA	40	50		mcd
Power Intensity	Po	If=20mA	2.0	2.8		mW
Peak Wavelength	λ_P	If=20mA	655	665	675	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	If=20mA		20		nm
RiseTime	tr	If=20mA		100		ns
FallTime	tf	If=20mA		100		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit : um]

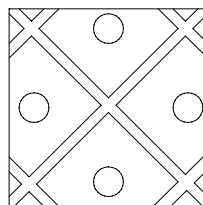
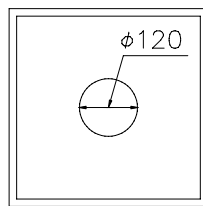


Fig.1 Electrode Pattern

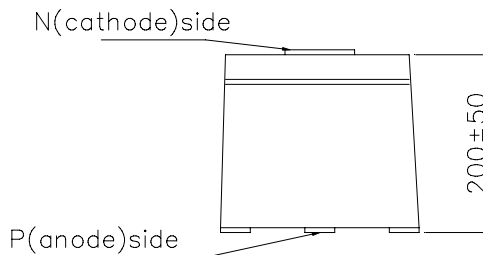
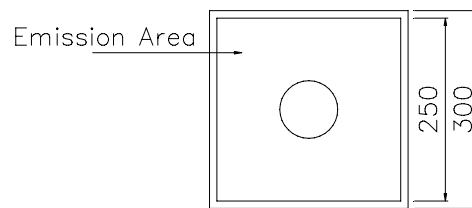


Fig.2 Chip size and Emission Area